N-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

BV_{DSS} / BV_{DGS}	$R_{DS(ON)}$ (max)	$I_{D(ON)}$ (min)	Order Number / Package	
			TO-39	TO-92
40V	8.0Ω	0.5A	—	—
60V	8.0Ω	0.5A	VN1306N2	—
100V	8.0Ω	0.5A	—	VN1310N3

Features

- ☐ Free from secondary breakdown
- ☐ Low power drive requirement
- ☐ Ease of paralleling
- ☐ Low C_{ISS} and fast switching speeds
- ☐ Excellent thermal stability
- ☐ Integral Source-Drain diode
- ☐ High input impedance and high gain
- ☐ Complementary N- and P-channel devices

Applications

- ☐ Motor controls
- ☐ Converters
- ☐ Amplifiers
- ☐ Switches
- ☐ Power supply circuits
- ☐ Drivers (relays, hammers, solenoids, lamps, memories, displays, bipolar transistors, etc.)

Absolute Maximum Ratings

Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

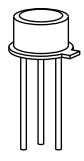
* Distance of 1.6 mm from case for 10 seconds.

Advanced DMOS Technology

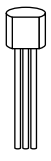
These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Package Options



TO-39
Case: DRAIN



TO-92

Note: See Package Outline section for dimensions.

Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ T_C = 25°C	θ_{jc} °C/W	θ_{ja} °C/W	I_{DR}*	I_{DRM}
TO-39	0.4A	1.4A	3.0W	41	125	0.4A	1.4A
TO-92	0.25A	1.3A	1.0W	125	170	0.25A	1.3A

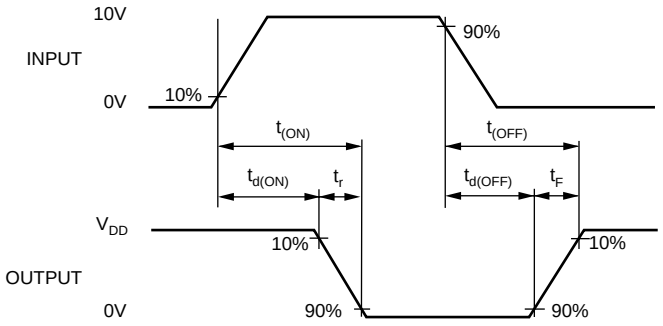
* I_D (continuous) is limited by max rated T_j.

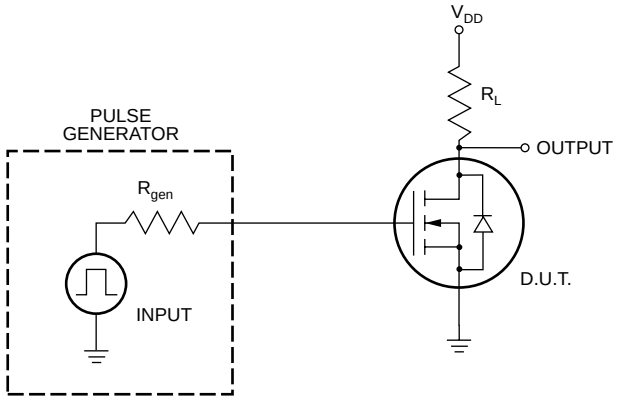
Electrical Characteristics (@ 25°C unless otherwise specified)

Symbol	Parameter		Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	VN1310	100			V	V_{GS} = 0V, I_D = 1mA
		VN1306	60				
		VN1304	40				
$V_{GS(th)}$	Gate Threshold Voltage		0.8		2.4	V	V_{GS} = V_{DS}, I_D = 1mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature			-3.9	-5.0	mV/°C	V_{GS} = V_{DS}, I_D = 1mA
I_{GSS}	Gate Body Leakage				100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero Gate Voltage Drain Current				1	µA	V_{GS} = 0V, V_{DS} = Max Rating
					100	µA	V_{GS} = 0V, V_{DS} = 0.8 Max Rating T_A = 125°C
$I_{D(ON)}$	ON-State Drain Current		0.25	0.6		A	V_{GS} = 5V, V_{DS} = 25V
			0.50	1.4			V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance			5.0	15	Ω	V_{GS} = 5V, I_D = 50mA
				5.0	8.0		V_{GS} = 10V, I_D = 500mA
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			0.8	2	%/°C	V_{GS} = 10V, I_D = 500mA
G_{FS}	Forward Transconductance		120			m℧	V_{DS} = 25V, I_D = 500mA
C_{ISS}	Input Capacitance			27	35	pF	V_{GS} = 0V, V_{DS} = 25V f = 1 MHz
C_{OSS}	Common Source Output Capacitance			13	15		
C_{RSS}	Reverse Transfer Capacitance			3	5		
$t_{d(ON)}$	Turn-ON Delay Time			2	5	ns	V_{DD} = 25V I_D = 500mA R_{GEN} = 25Ω
t_r	Rise Time			2	5		
$t_{d(OFF)}$	Turn-OFF Delay Time			2	6		
t_f	Fall Time			2	5		
V_{SD}	Diode Forward Voltage Drop			1.0	1.3	V	V_{GS} = 0V, I_{SD} = 0.5A
t_{rr}	Reverse Recovery Time			350		ns	V_{GS} = 0V, I_{SD} = 0.5A

Notes:
1. All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300µs pulse, 2% duty cycle.)
2. All A.C. parameters sample tested.

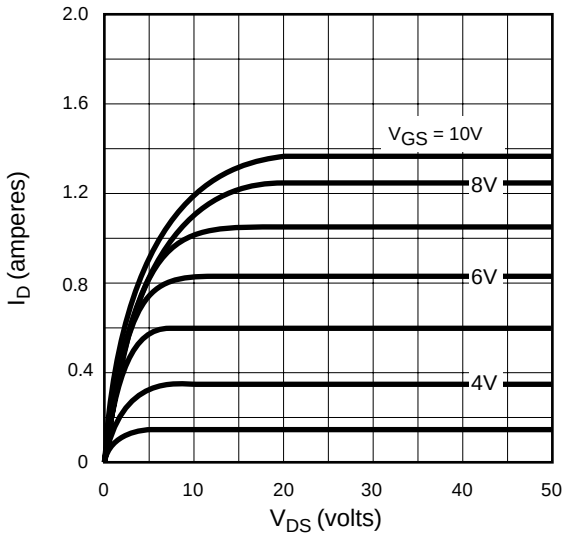
Switching Waveforms and Test Circuit



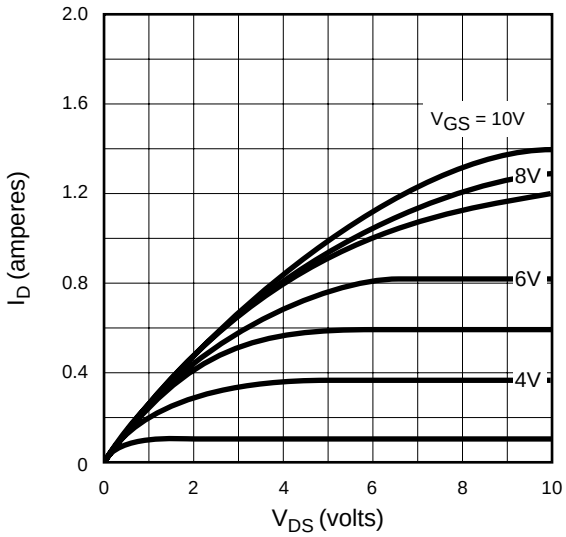


Typical Performance Curves

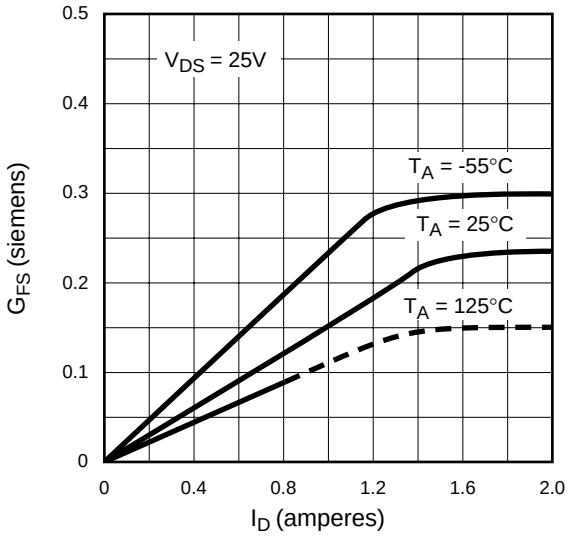
Output Characteristics



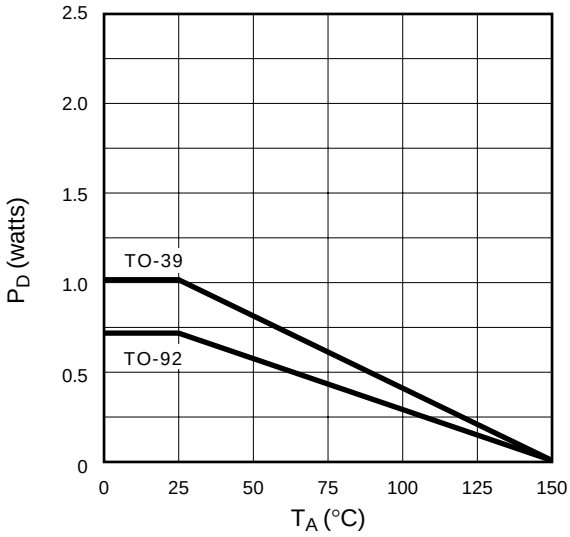
Saturation Characteristics



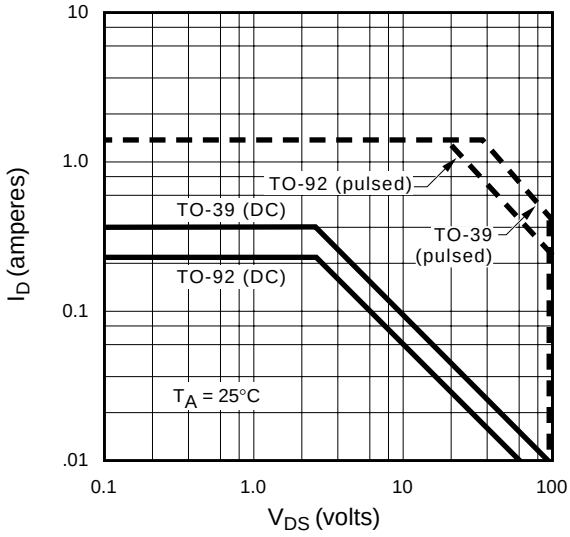
Transconductance vs. Drain Current



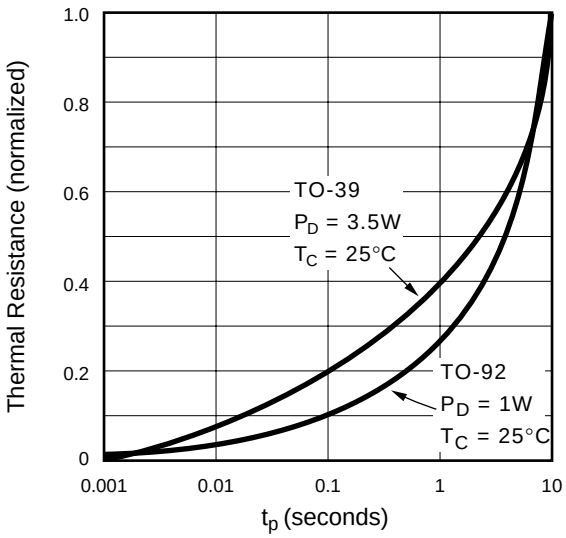
Power Dissipation vs. Ambient Temperature



Maximum Rated Safe Operating Area



Thermal Response Characteristics



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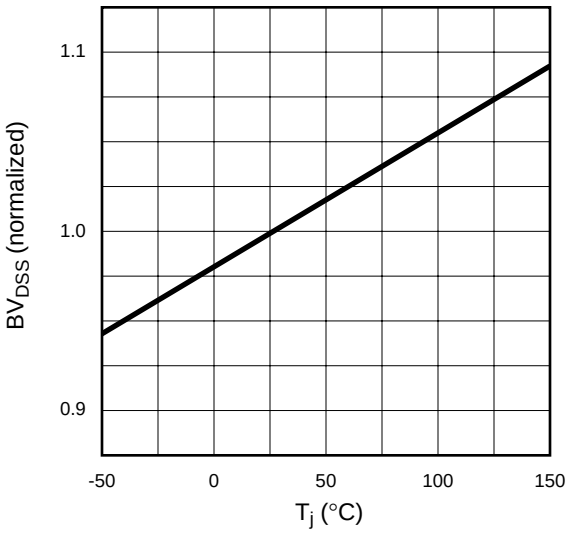
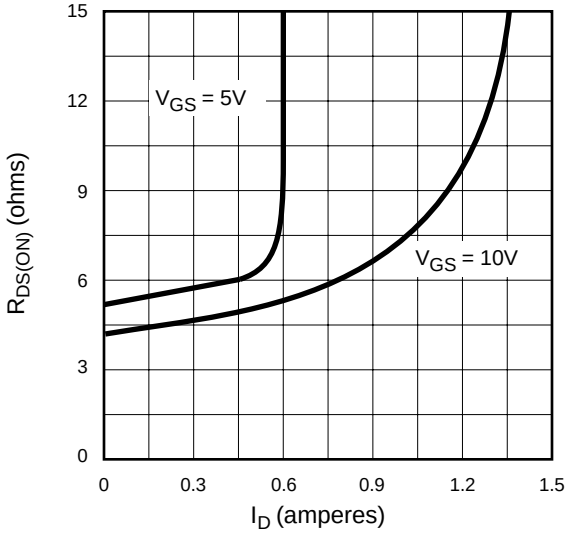
Typical Performance Curves

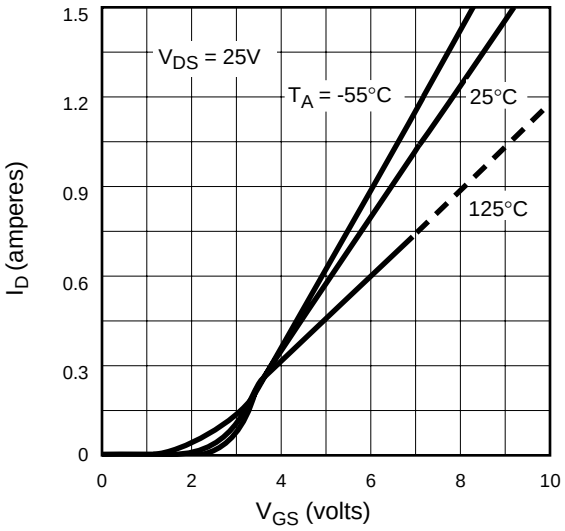
BV$_{DSS}$ Variation with Temperature



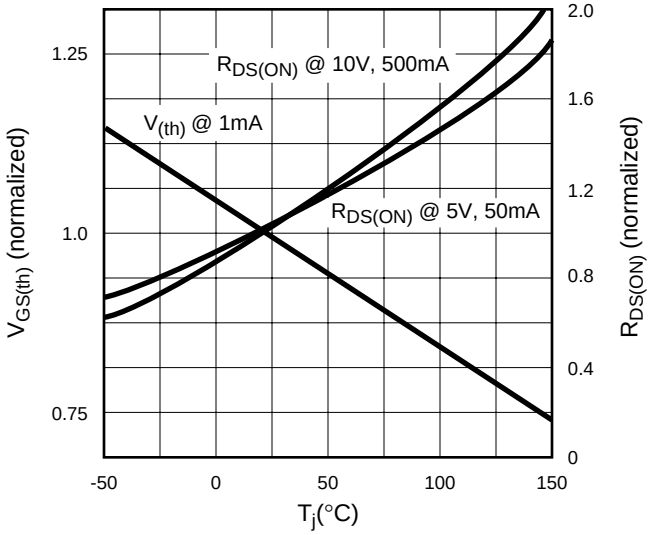
On-Resistance vs. Drain Current



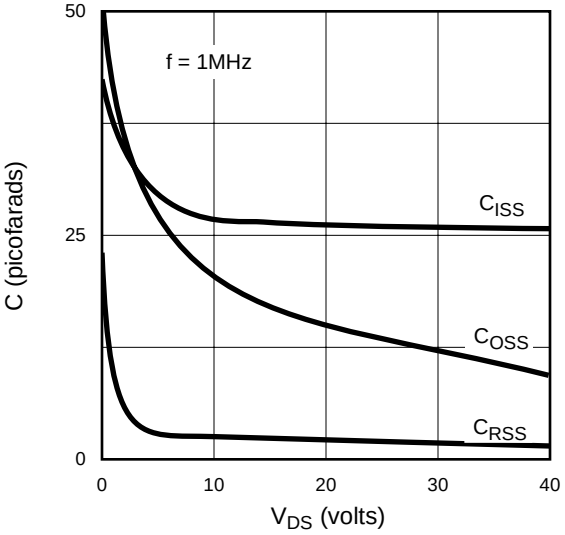
Transfer Characteristics



V$_{(th)}$ and R$_{DS}$ Variation with Temperature



Capacitance vs. Drain-to-Source Voltage



Gate Drive Dynamic Characteristics

